

Notice of References Cited	Application/Control No. 10/618,024	Applicant(s)/Patent Under Reexamination VAUDO ET AL.	
	Examiner W. David Coleman	Art Unit 2823	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,407,409	06-2002	Cho et al.	257/78
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
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	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kelly et al., "Large Free-Standing GaN Substrates by Hydride Vapor Phase Epitaxy and Laser-Induced Liftoff", Japanese Journal of Applied Physics, Part 2, No. 3A, March 1999, pp. L217-L219.
	V	Valudo et al., " Characteristics of semi-insulating, Fe-doped GaN substrates", Physics Solid State (a), Wiley-VCH Verlag GmbH & Co. KGaA, Weinheim, (November 2003), No. 1, vol. 200, pp. 18-21.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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